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Supporting Information

Boron-Interstitial Doped C_2N Layer as a Metal-Free Electrocatalyst for N_2 Fixation: A Computational Study

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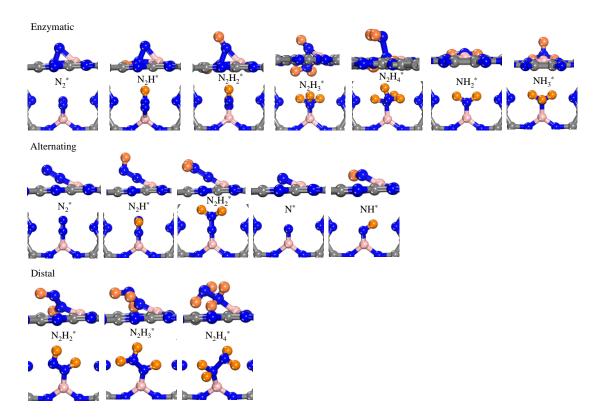


Figure S1. The side and top views of the involved NRR intermediates on B_{int} surface along the enzymatic, alternating, and distal pathways.

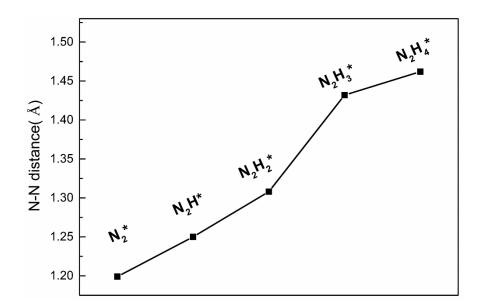


Figure S2. The variation of N-N bond lengths of various NRR intermediates on B_{int} along the enzymatic pathway.

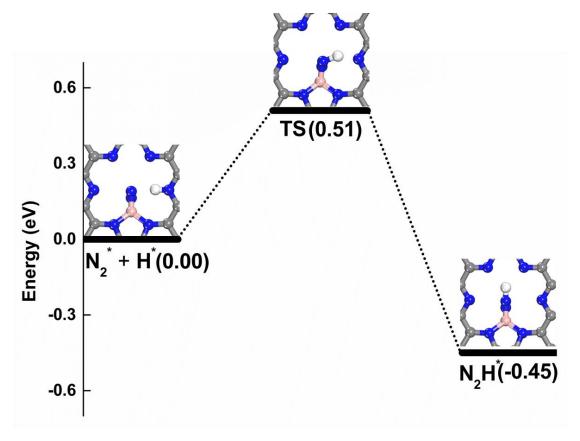


Figure S3. The reaction pathway of H-transfer from the N atom around B site to the adsorbed N_2 molecule. TS denotes the transition state.

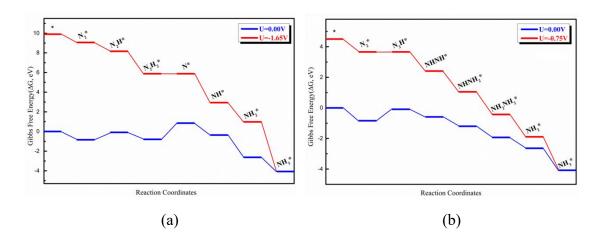


Figure S4. The free energy profiles of NRR on B_N -doped C_2N layer along the (a) distal and (b) alternating pathways.

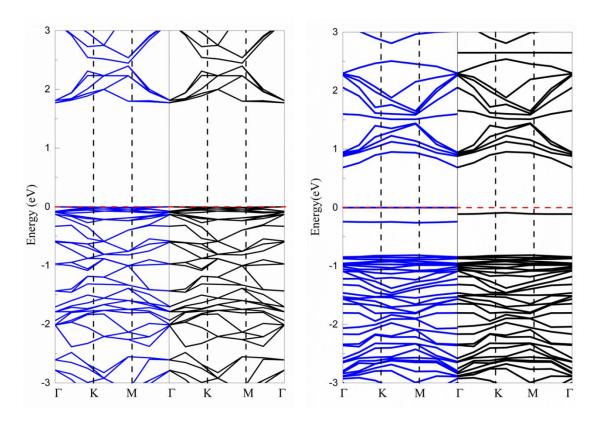


Figure S5. The computed band structures of (a) pure and (b) B_{int} -doped C_2N layers.

The Fermi level is set as zero in dotted lines.